

T0620H-6F 6A TRIAC

Rev.A.1.0

DESCRIPTION:

The T0620H-6F triac is suitable for general purpose AC switching. It can be used as an ON/OFF function in applications such as heating regulation, induction motor starting circuits, for phase control operation in light dimmers, motor speed controllers. Compared to traditional triacs, T0620H-6F provides a very high switching capability up to junction temperatures of 150°C. By using an external plastic package, T0620H-6F provides a rated insulation voltage of 2000 VRMS, complying with UL standards (File ref: E252906). Package TO-220F is RoHS compliant.

TO-220F Insulated 123 T2(2) T1(1) G(3)

MAIN FEATURES

Symbol	Value	Unit
I _{T(RMS)}	6	Α
V _{DRM} /V _{RRM}	600	V
I GT / /	20/20/20	mA

ABSOLUTE MAXIMUM RATINGS

Parameter	Symbol	Value	Unit
Storage junction temperature range	T _{stg}	-40-150	
Operating junction temperature range	Tj	-40-150	
Repetitive peak off-state voltage (T _j =25)	V_{DRM}	600	V
Repetitive peak reverse voltage (T _j =25)	V _{RRM}	600	V
RMS on-state current (T _C 120)	I _{T(RMS)}	6	Α
Non repetitive surge peak on-state current (full cycle , t _p =20ms , T _j =25)	1	60	А
Non repetitive surge peak on-state current (full cycle, $t_p=16.6ms$, $T_j=25$)	Ітѕм	66	A
I ² t value for fusing (t _p =10ms , T _j =25)	l ² t	18	A ² s
Critical rate of rise of on-state current ($I_G=2 \times I_{GT}$, $f=100Hz$, $T_j=150$)	dl/dt	80	A/µs
Peak gate current (t _p =20µs , T _j =150)	Ідм	4	Α

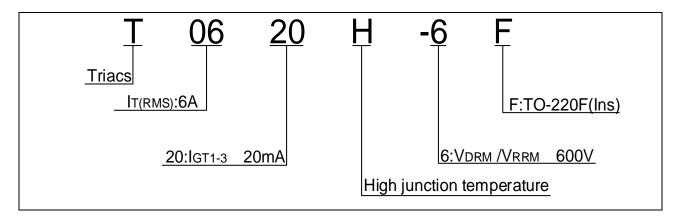
T0620H-6F

Average gate power dissipation (T _j =150)	P _{G(AV)}	1	W
Peak gate power	P _{GM}	10	W
Peak pulse voltage (T _i =25 ; non-repetitive,off-state;FIG.7)	V_{pp}	3	kV

ELECTRICAL CHARACTERISTICS (T_j=25 unless otherwise specified)

G M

ORDERING INFORMATION



MARKING

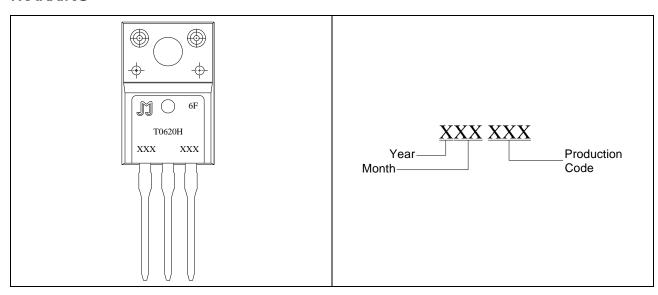


FIG.1 Maximum power dissipation versus RMS on-state current

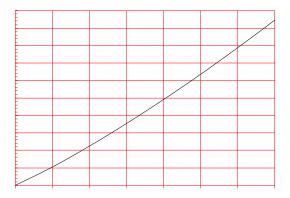


FIG.3: Surge peak on-state current versus number of cycles

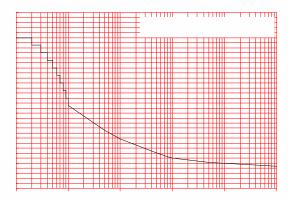


FIG.5: Non-repetitive surge peak on-state current for a sinusoidal pulse with width t_p <20ms, and corresponding value of I^2t (dI/dt<80A/ μ s)

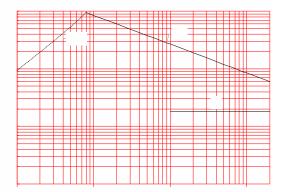


FIG.2: RMS on-state current versus case temperature

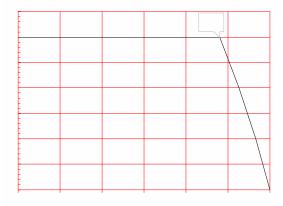


FIG.4: On-state characteristics

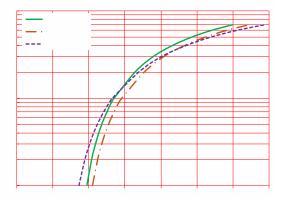


FIG.6: Relative variations of gate trigger current, holding current and latching current versus junction temperature

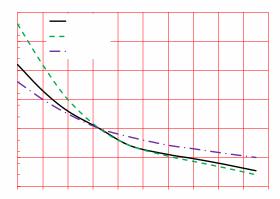
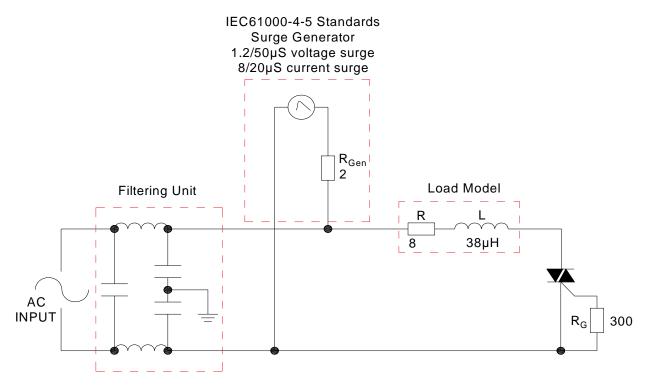


FIG.7 Test circuit for inductive and resistive loads to IEC-61000-4-5 standards



SHAPING AND SOLDERING PARAMETERS

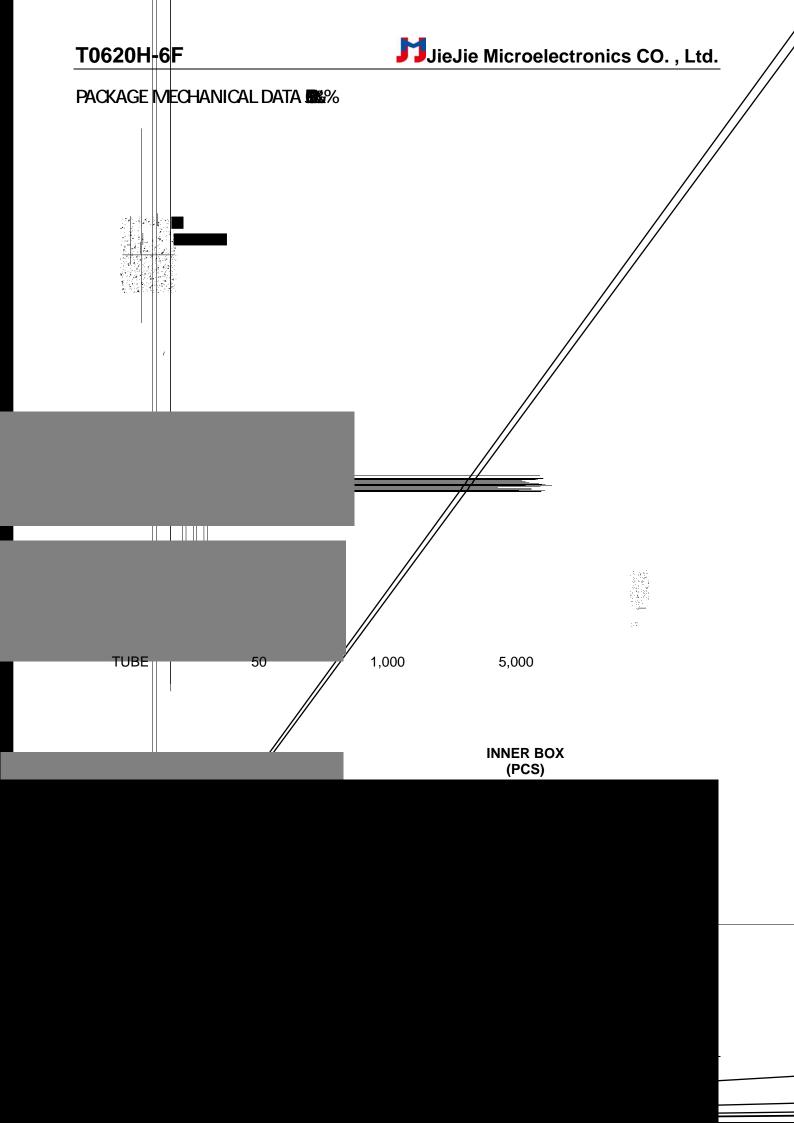
Refer to Instructions for installation of plastic-sealed in-line power devices released by JieJie

ORDERING INFORMATION

Order code	Voltage	IGT(mA)		Base qty.	Delivery
	VDRM/VRRM (V)		Package	(pcs)	mode
T0620H-6F	600	20	TO-220F(Ins)	50	Tube

Document Revision History

Date





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